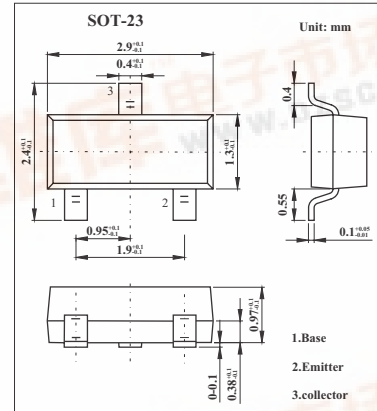


SMD Type Transistors

NPN Transistor
2SC3052

Features

- Collector current :Ic=0.2A
- Power dissipation :Pc=0.15W



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	50	V
Collector-emitter voltage	V _{CE0}	50	V
Emitter-base voltage	V _{EB0}	6	V
Collector current	I _c	200	mA
power dissipation *	P _c	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* . 0.7 mmx16 cm² ceramic substrate

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _c = 100 μ A, I _E = 0	50			V
Collector-emitter breakdown voltage	V _{CE0}	I _C = 100 μ A, I _B = 0	50			V
Emitter-base breakdown voltage	V _{EB0}	I _E = 100 μ A, I _C = 0	6			V
Collector cut-off current	I _{CB0}	V _{CB} = 50V, I _E = 0			0.1	μ A
Emitter cut-off current	I _{EB0}	V _{EB} = 6V, I _C = 0			0.1	μ A
DC current gain	h _{FE}	V _{CE} = 6V, I _C = 1mA	150		800	
		V _{CE} = 6V, I _C = 0.1mA	50			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 100mA, I _B = 10mA			0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 100mA, I _B = 10mA			1	V
Collector output capacitance	C _{ob}	V _{CE} = 6V, I _E = 0, f = 1MHz			4	pF
Noise figure	NF	V _{CE} = 6V, I _E = -0.1mA, f = 1KHz, R _G = 2K Ω			15	dB
Transition frequency	f _t	V _{CE} = 6V, I _C = 10mA	180			MHz

hFE Classification

Marking	LE	LF	LG
Rank	E	F	G
hFE	150 to 300	250 to 500	400 to 800

